

TOSHIBA THYRISTOR SILICON DIFFUSED TYPE

# SF2500EX22

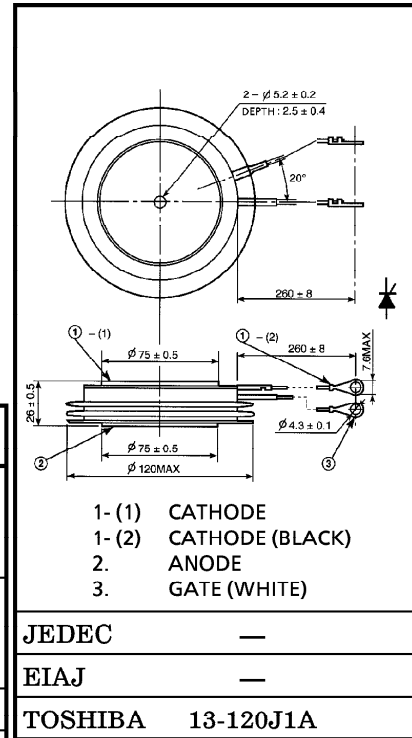
HIGH POWER CONTROL APPLICATIONS

Unit in mm

- Repetitive Peak Off-State Voltage :  $V_{DRM}$
- Repetitive Peak Reverse Voltage :  $V_{RRM}$  } = 2500V
- Average On-State Current :  $I_T(AV) = 2500A$
- Turn-Off Time :  $t_q = 400\mu s$  (Max.)
- Critical Rate of Rise of On-State Current :  $di/dt = 250A/\mu s$
- Critical Rate of Rise of Off-State Voltage :  $dv/dt = 1500V/\mu s$
- Flat Package

**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	$V_{DRM}$ $V_{RRM}$	2500	V
Non-Repetitive Peak Reverse Voltage (Non-Repetitive < 5ms, $T_j = 0 \sim 125^\circ C$ )	$V_{RSM}$	2750	V
R.M.S On-State Current	$I_T(RMS)$	3925	A
Average On-State Current	$I_T(AV)$	2500	A
Peak One Cycle Surge On-State Current (Non-Repetitive)	$I_{TSM}$	45000 (50Hz)	A
		50000 (60Hz)	
$I^2t$ Limit Value	$I^2t$	$1 \times 10^7$	$A^2s$
Critical Rate of Rise of On-State Current (Note)	$di/dt$	250	$A/\mu s$
Peak Gate Power Dissipation	$P_{GM}$	30	W
Average Gate Power Dissipation	$P_G(AV)$	4	W
Peak Forward Gate Current	$I_{GM}$	6	A
Peak Forward Gate Voltage	$V_{FGM}$	30	V
Peak Reverse Gate Voltage	$V_{RGM}$	5	V
Junction Temperature	$T_j$	$-40 \sim 125$	$^\circ C$
Storage Temperature Range	$T_{stg}$	$-40 \sim 125$	$^\circ C$
Mounting Force	—	$39.2 \pm 3.9$	kN



JEDEC	—
EIAJ	—
TOSHIBA	13-120J1A

Weight : 1350g

Note :  $V_D = 1/2$  Rated,  $T_j = 120^\circ C$ , Gate Supply ( $V_G = 15V$ ,  $R_G = 8\Omega$ ,  $t_r \leq 1\mu s$ )

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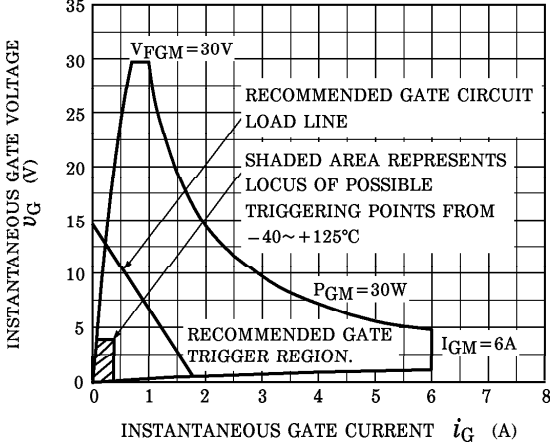
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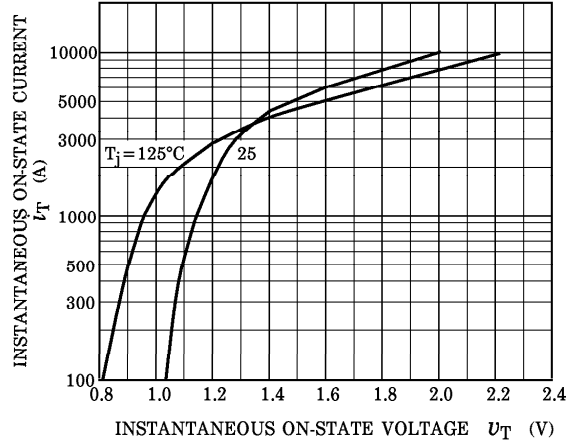
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT	
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	$I_{DRM}$ $I_{RRM}$	$V_{DRM} = V_{RRM} = \text{Rated}$ , $T_j = 125^\circ\text{C}$	—	120	mA	
Peak On-State Voltage	$V_{TM}$	$I_{TM} = 8000\text{A}$ , $T_j = 25^\circ\text{C}$	—	1.82	V	
Gate Trigger Voltage	$V_{GT}$	$V_D = 12\text{V}$ , $R_L = 6\Omega$	$T_j = -40^\circ\text{C}$	—	4.0	V
			$T_j = 25^\circ\text{C}$	—	2.5	
Gate Trigger Current	$I_{GT}$		$T_j = -40^\circ\text{C}$	—	400	mA
			$T_j = 25^\circ\text{C}$	—	250	
Gate Non-Trigger Voltage	$V_{GD}$	$V_D = 1/2 \text{ Rated}$ , $T_j = 125^\circ\text{C}$	0.2	—	V	
Gate Non-Trigger Current	$I_{GD}$		5	—	mA	
Delay Time	$t_d$	$V_D = 0.5 \text{ Rated}$ , $T_j = 25^\circ\text{C}$ Gate Supply ( $V_G = 15\text{V}$ , $R_G = 8\Omega$ , $t_r \leq 1\mu\text{s}$ )	—	5	$\mu\text{s}$	
Gate Turn-On Time	$t_{gt}$		—	10	$\mu\text{s}$	
Turn-Off Time	$t_q$	$I_T = 1200\text{A}$ , $V_R \geq 200\text{V}$ $dv/dt = 25\text{V}/\mu\text{s}$ , $T_j = 115^\circ\text{C}$ $V_{DRM} = 1/2 \text{ Rated}$	—	400	$\mu\text{s}$	
Holding Current	$I_H$	$T_j = 25^\circ\text{C}$ , $R_L = 6\Omega$	—	300	mA	
Critical Rate of Rise of Off-State Voltage	$dv/dt$	$V_{DRM} = 1/2 \text{ Rated}$ , $T_j = 125^\circ\text{C}$ Gate Open Exponential Rise	1500	—	$\text{V}/\mu\text{s}$	
Thermal Resistance	$R_{th(j-f)}$	Junction to Fin	—	0.0125	$^\circ\text{C}/\text{W}$	

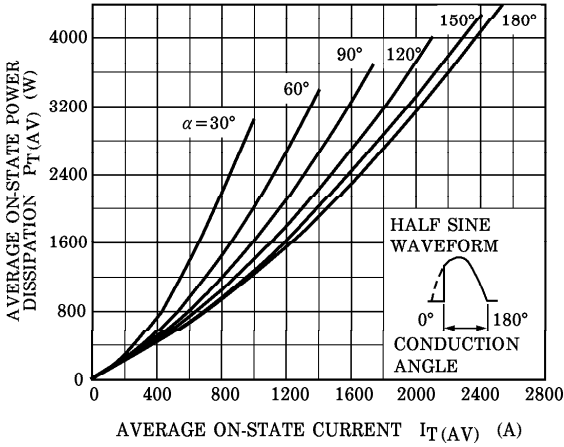
GATE TRIGGER CHARACTERISTIC



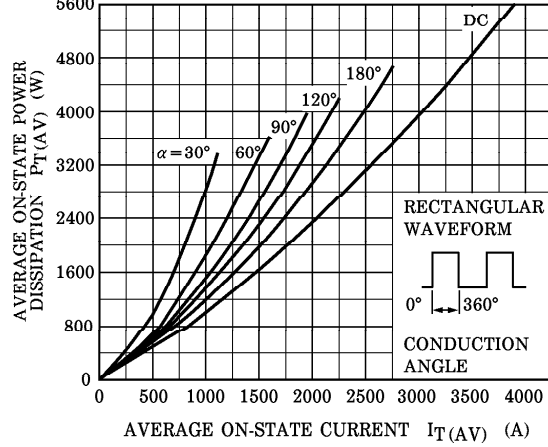
$i_T - v_T$



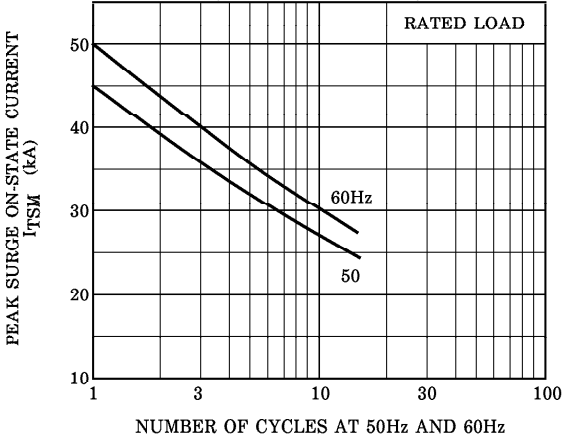
$P_T(AV) - I_T(AV)$



$P_T(AV) - I_T(AV)$



SURGE ON-STATE CURRENT (NON-REPETITIVE)



TRANSIENT THERMAL IMPEDANCE (JUNCTION TO FIN)

